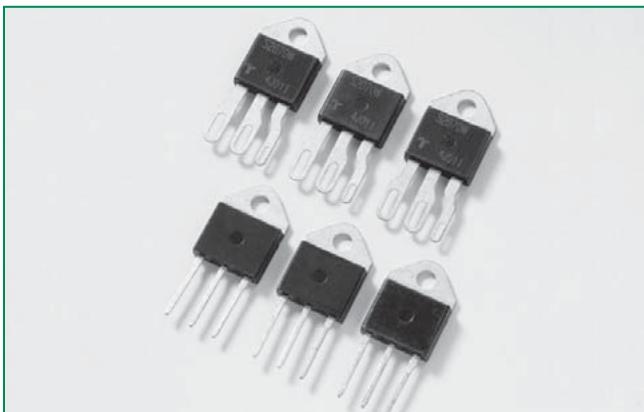


## Qxx40xx Series



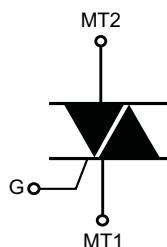
### Agency Approval

Agency	Agency File Number
	K & J Packages: E71639

### Main Features

Symbol	Value	Unit
$I_{TRMS}$	40	A
$V_{DRM}/V_{RRM}$	400 to 1000	V
$I_{GT(A1)}$	50 to 100	mA

### Schematic Symbol



### Description

40 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

### Features & Benefits

- RoHS Compliant
- Surge capability up to 400A
- Glass – passivated junctions
- Voltage capability up to 1000V
- Electrically isolated K & J -Packages are UL recognized for 2500Vrms

### Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

**Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)**

Symbol	Parameter		Value	Unit
$I_{TRMS}$	RMS on-state current (full sine wave)	Qxx40x7 Qxx40xH6	$T_c = 75^\circ\text{C}$	40
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_j$ initial = $25^\circ\text{C}$ )	$f = 50 \text{ Hz}$	$t = 20 \text{ ms}$	335
		$f = 60 \text{ Hz}$	$t = 16.7 \text{ ms}$	400
$I^2t$	$I^2t$ Value for fusing		$t_p = 8.3 \text{ ms}$	664
$dI/dt$	Critical rate of rise of on-state current ( $I_G = 2 \times I_{GT}$ , $t_r \leq 100 \text{ ns}$ )	$f = 120 \text{ Hz}$	$T_j = 125^\circ\text{C}$	150
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_j = 125^\circ\text{C}$	4
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	0.8
$T_{stg}$	Storage temperature range			-40 to 150
$T_j$	Operating junction temperature range			-40 to 125

Note: xx = voltage, x = package

**Electrical Characteristics ( $T_j = 25^\circ\text{C}$ , unless otherwise specified) — Alternistor Triac (3 Quadrants)**

Symbol	Test Conditions	Quadrant		Value			Unit
				Qxx40xH6	Qxx40K5	Qxx40x7	
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I - II - III	MAX.	80	50	100	mA
$V_{GT}$		I - II - III	MAX.	1.3	1.3	2.0	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^\circ\text{C}$	I - II - III	MIN.	0.2			V
$I_H$	$I_T = 400\text{mA}$		MAX.	80	75	100	mA
$dv/dt$	$V_D = V_{DRM}$ Gate Open $T_j = 125^\circ\text{C}$	400V	MIN.	600	500	700	V/ $\mu\text{s}$
		600V		500	475	625	
		800V		475	400	575	
	$V_D = V_{DRM}$ Gate Open $T_j = 100^\circ\text{C}$	1000V		--	--	500	
( $dv/dt$ )c	$(di/dt)c = 21.6 \text{ A/ms}$ $T_j = 125^\circ\text{C}$		MIN.	30	20	50	V/ $\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = $15\mu\text{s}$ $I_T = 56.6\text{A(pk)}$		TYP.	5			$\mu\text{s}$

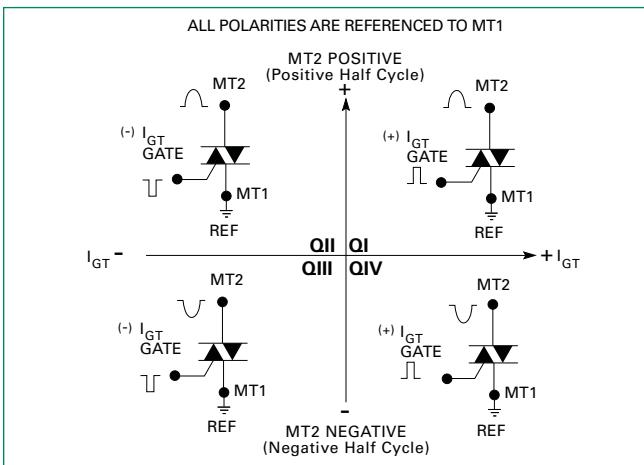
**Static Characteristics**

Symbol	Test Conditions		Value	Unit
$V_{TM}$	$I_{TM} = 56.6\text{A}$ $t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.8
$I_{DRM}$ $I_{RRM}$	$V_D = V_{DRM} / V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	20
		$T_j = 125^\circ\text{C}$	MAX.	5
		$T_j = 100^\circ\text{C}$	MAX.	5

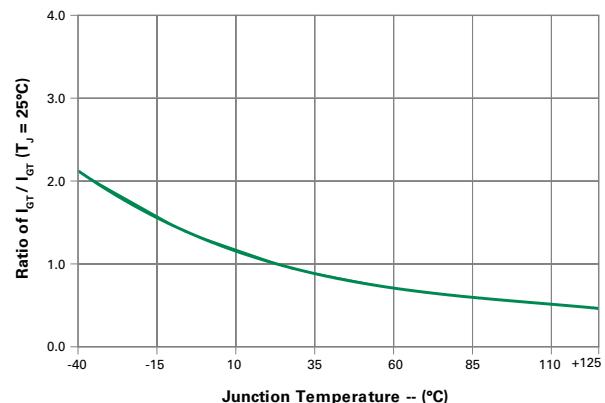
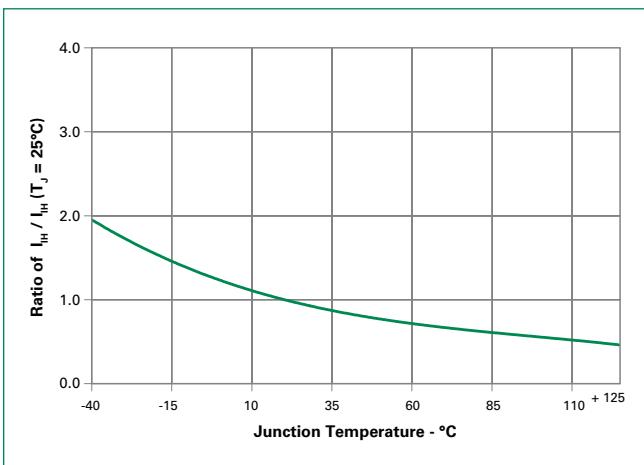
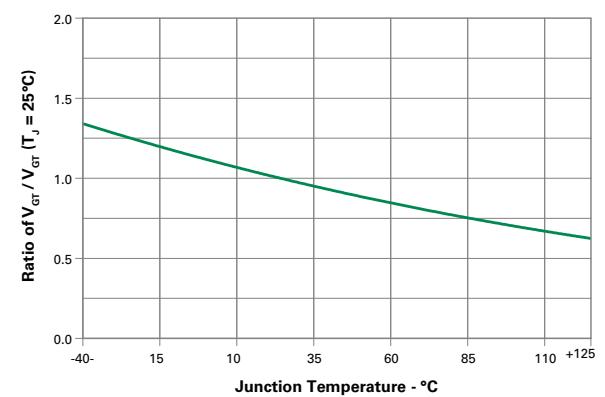
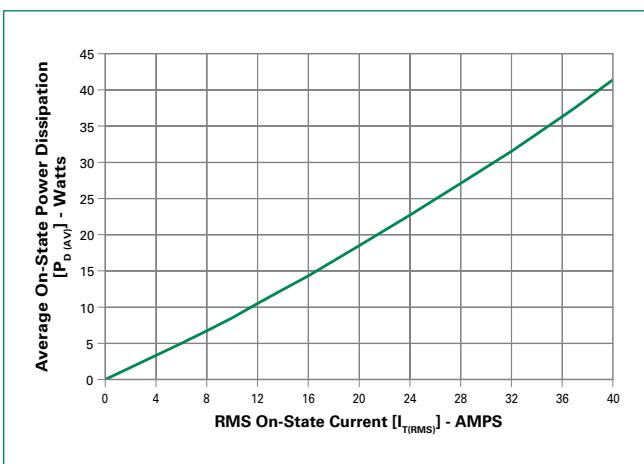
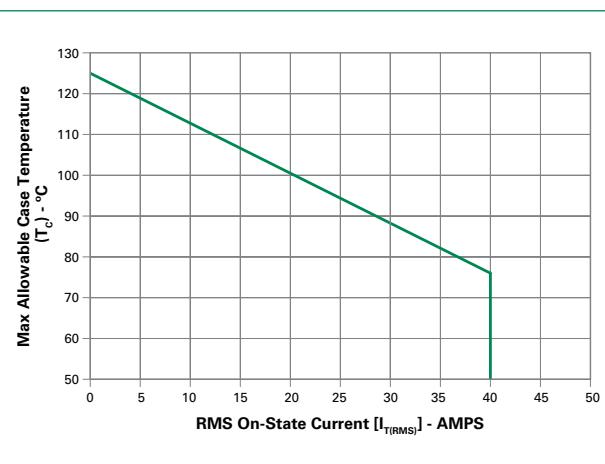
**Thermal Resistances**

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx40KH6 Qxx40K5 Qxx40K7	0.97	°C/W
		Qxx40JH6 Qxx40J7	0.95	

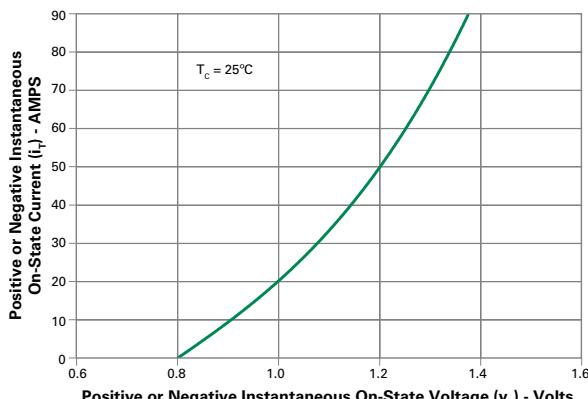
Note: xx = voltage

**Figure 1: Definition of Quadrants**


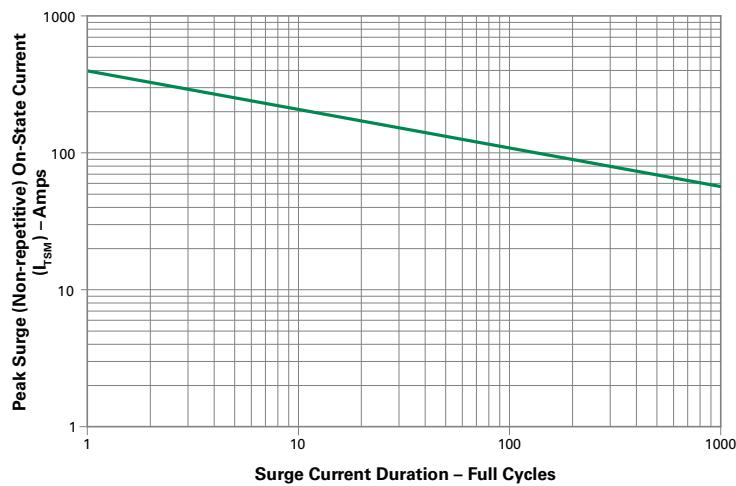
Note: Alternistors will not operate in QIV

**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**

**Figure 3: Normalized DC Holding Current vs. Junction Temperature**

**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**

**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**

**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**


**Figure 7: On-State Current vs. On-State Voltage (Typical)**



**Figure 8: Surge Peak On-State Current vs. Number of Cycles**



Supply Frequency: 60Hz Sinusoidal  
Load: Resistive  
RMS On-State [ $I_{T(RMS)}$ ]: Max Rated Value at Specific Case Temperature

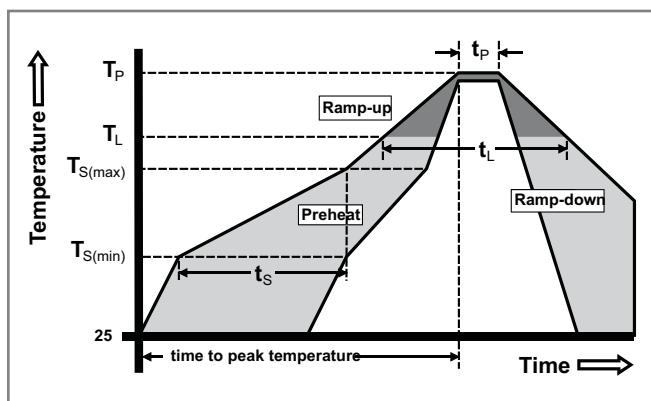
Notes:

- 1) Gate control may be lost during and immediately following surge current interval.
- 2) Overload may not be repeated until junction temperature has returned to steady-state rated value.

Note: xx = voltage

### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	-Temperature Min ( $T_{s(\min)}$ )	150°C
	-Temperature Max ( $T_{s(\max)}$ )	200°C
	-Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
Reflow	$T_{s(\max)}$ to $T_L$ - Ramp-up Rate	5°C/second max
	-Temperature ( $T_L$ ) (Liquidus)	217°C
	-Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

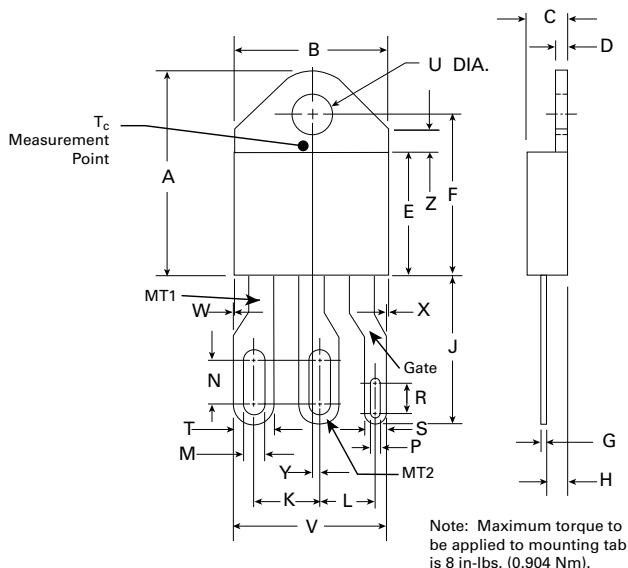
<b>Terminal Finish</b>	100% Matte Tin-plated.
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0.
<b>Lead Material</b>	Copper Alloy

### Design Considerations

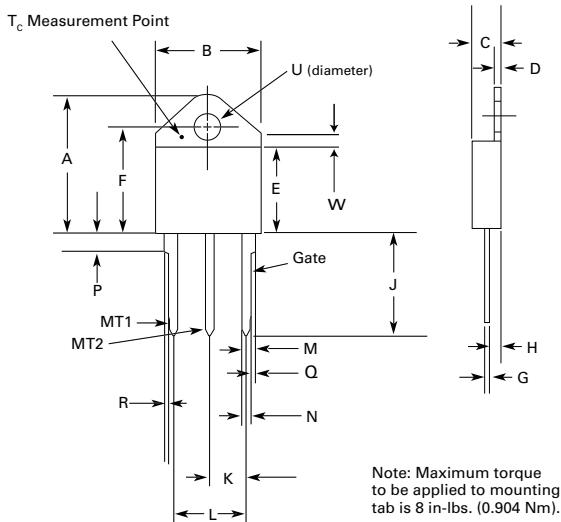
Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Thermal Shock</b>	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
<b>Autoclave</b>	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

**Dimensions — TO-218X (J Package) — Isolated Mounting Tab**


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.164	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

**Dimensions — TO-218AC (K Package) — Isolated Mounting Tab**


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.164	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

**Product Selector**

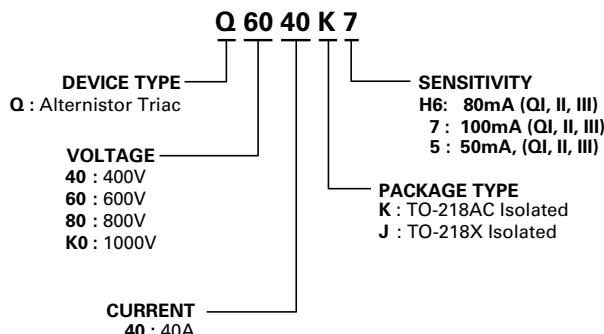
Part Number	Voltage				Gate Sensitivity Quadrants		$I_{T(RMS)}$	Type	Package
	400V	600V	800V	1000V	I - II - III	IV			
Qxx40KH6	X	X	X	X	80mA		40A	Alternistor Triac	TO-218AC
Qxx40JH6	X	X	X		80mA		40A	Alternistor Triac	TO-218X
Qxx40K5	X	X	X		50mA		40A	Alternistor Triac	TO-218AC
Qxx40K7	X	X	X	X	100 mA		40A	Alternistor Triac	TO-218AC
Qxx40J7	X	X	X		100 mA		40A	Alternistor Triac	TO-218X

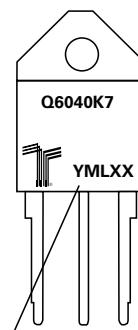
Note: xx = Voltage

**Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx40KH6TP	Qxx40KH6	4.40g	Tube	250 (25 per tube)
Qxx40JH6TP	Qxx40JH6	5.23g	Tube	250 (25 per tube)
Qxx40K5TP	Qxx40K5	4.40g	Tube	250 (25 per tube)
Qxx40K7TP	Qxx40K7	4.40g	Tube	250 (25 per tube)
Qxx40J7TP	Qxx40J7	5.23g	Tube	250 (25 per tube)

Note: xx = Voltage

**Part Numbering System**

**Part Marking System**

 TO-218 AC - (K Package)  
 TO-218 X - (J Package)

 Date Code Marking  
 Y:Year Code  
 M:Month Code  
 L:Location Code  
 XX: Lot Serial Code